

AMENDMENTS TO THE SPECIFICATION:

Page 6, please amend the paragraph, beginning on line 27, as follows:

--Japanese Laid Open Patent Application (JP-A-Heisei 10-4227) discloses a magnetic tunnel junction capable of controlling a magnetic response. The magnetic tunnel junction element of the conventional example includes a substrate, a first electrode, a second electrode, and an insulating tunnel layer. The first electrode has a fixed ferromagnetic layer and anti-ferromagnetic layer. The fixed ferromagnetic layer is formed on the substrate and flat. The anti-ferromagnetic layer is adjacent to the fixed ferromagnetic layer to fix the magnetized direction of the fixed ferromagnetic layer in a preferred direction and prevents the reversion of magnetization direction under an applied magnetic field. The second electrode has a flat free ferromagnetic layer capable of freely reversible in the magnetized direction under the applied magnetic field. The insulating tunnel layer is provided between the fixed ferromagnetic layer and the free ferromagnetic layer to allow a tunnel current to flow in the direction vertical to the fixed ferromagnetic layer and free ferromagnetic layer. The insulating tunnel layer has a side circumference to prevent the fixed ferromagnetic layer or free ferromagnetic layer from extending, exceeding the side circumference of the insulating tunnel layer. Moreover, the ~~insulating~~ insulating tunnel layer is held in another plane in which the fixed ferromagnetic layer and

free ferromagnetic layer are separate from each other without overlapping.--

Page 13, please amend the paragraph, beginning on line 23, as follows:

--Also, in another aspect of the present invention, a magnetic memory manufacturing method forms a multi-layer film included in a magnetic element on the upside of a substrate, etches the multi-layer film into a predetermined pattern up to a predetermined depth, forms the upper portion structure of the magnetic element as a part of the magnetic element, forms the sidewall insulating film to surround the upper portion structure of the magnetic element, etches the multi-layer film by using the sidewall ~~insulating~~ insulating film and the upper portion structure of the magnetic element as a mask, and forms the lower portion structure of the magnetic element as a remaining portion of the magnetic element.--

Page 14, please amend the paragraph, beginning on line 10, as follows:

-- Also, in case of the magnetic memory manufacturing method of the present invention, the lower portion structure of the magnetic element may include a first magnetic layer formed on a conductive portion and the upside of the conductive portion. The upper portion structure of the magnetic element may include an ~~insulating~~ insulating layer and a second magnetic layer formed on the upside of the insulating layer.--

Page 21, please amend the paragraph, beginning on line 9, as follows:

-- Next, as shown in Fig. 2D, dry etching is applied to the protection film 18 under a predetermined condition and the sidewall 19 is formed. The predetermined condition is experimentally determined in accordance with the structure of the magnetic element or the characteristic of the protection film 18. Thereby, the sides of the upper conductive layer 17', the free ferromagnetic layer 16', and the ~~insulating~~ insulating layer 15' are not exposed to an etching atmosphere in the later etching steps. Therefore, it is possible to avoid deterioration of film quality due to etching gas, attachment of an etched substance to the side (side attachment), or and abnormal electrical characteristic due to the attachment in the substance of the free ferromagnetic layer 16' and the ~~insulating~~ insulating layer 15'.--